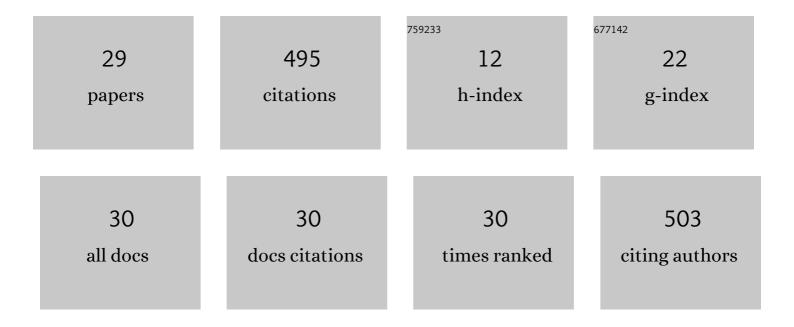
Vincent LaBella

List of Publications by Year in descending order

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VINCENT LARELLA

#	Article	IF	CITATIONS
1	Spatially Resolved Spin-Injection Probability for Gallium Arsenide. Science, 2001, 292, 1518-1521.	12.6	94
2	Enhancing the Studentâ€Instructor Interaction Frequency. Physics Teacher, 2002, 40, 535-541.	0.3	43
3	Measurement of hot-electron scattering processes at Au/Si(100) Schottky interfaces by temperature-dependent ballistic-electron-emission microscopy. Physical Review B, 1996, 53, 3952-3959.	3.2	40
4	Monte Carlo derived diffusion parameters for Ga on the GaAs(001)- (2×4) surface: A molecular beam epitaxy–scanning tunneling microscopy study. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2000, 18, 1526-1531.	2.1	40
5	Fermi Level Manipulation through Native Doping in the Topological Insulator Bi ₂ Se ₃ . ACS Nano, 2018, 12, 6310-6318.	14.6	37
6	Schottky barrier height measurements of Cu/Si(001), Ag/Si(001), and Au/Si(001) interfaces utilizing ballistic electron emission microscopy and ballistic hole emission microscopy. AlP Advances, 2013, 3, .	1.3	31
7	Reflection high-energy electron diffraction and scanning tunneling microscopy study of InP(001) surface reconstructions. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2000, 18, 1492-1496.	2.1	27
8	Combined molecular beam epitaxy low temperature scanning tunneling microscopy system: Enabling atomic scale characterization of semiconductor surfaces and interfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1684.	1.6	27
9	Enabling electron diffraction as a tool for determining substrate temperature and surface morphology. Applied Physics Letters, 2001, 79, 3065-3067.	3.3	24
10	Role of As[sub 4] in Ga diffusion on the GaAs(001)-(2×4) surface: A molecular beam epitaxy-scanning tunneling microscopy study. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1778.	1.6	22
11	Measurement of the hot electron attenuation length of copper. Applied Physics Letters, 2010, 96, .	3.3	18
12	Time dependent changes in Schottky barrier mapping of the W/Si(001) interface utilizing ballistic electron emission microscopy. Journal of Applied Physics, 2015, 117, .	2.5	12
13	Hot-electron transport studies of the Ag/Si(001) interface using ballistic electron emission microscopy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 643-646.	2.1	10
14	Nanoscale mapping of the W/Si(001) Schottky barrier. Journal of Applied Physics, 2014, 116, 023705.	2.5	9
15	A UNION OF THE REAL-SPACE AND RECIPROCAL-SPACE VIEW OF THE GaAs(001) SURFACE. International Journal of Modern Physics B, 2001, 15, 2301-2333.	2.0	8
16	Signatures of the semiconductor crystallographic orientation on the charge transport across non-epitaxial diodes. Applied Physics Letters, 2012, 100, .	3.3	8
17	Relating spatially resolved maps of the Schottky barrier height to metal/semiconductor interface composition. Journal of Applied Physics, 2016, 119, .	2.5	7
18	Microscopic structure of spontaneously formed islands on the GaAs(001)-(2×4) reconstructed surface. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1640.	1.6	6

VINCENT LABELLA

#	Article	IF	CITATIONS
19	Nanoscale Schottky barrier mapping of thermally evaporated and sputter deposited W/Si(001) diodes using ballistic electron emission microscopy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, .	1.2	6
20	Detection of silicide formation in nanoscale visualization of interface electrostatics. Applied Physics Letters, 2017, 110, 141606.	3.3	6
21	Efficient circuit design for low power energy harvesting. AIP Advances, 2020, 10, .	1.3	6
22	Pulsed-N2 assisted growth of 5-20 nm thick <i>\hat{l}^2</i> -W films. AIP Advances, 2015, 5, .	1.3	4
23	Synthesis and properties of ferromagnetic nanostructures embedded within a high-quality crystalline silicon matrix via ion implantation and nanocavity assisted gettering processes. Journal of Applied Physics, 2014, 116, 054306.	2.5	3
24	Nanoscale Schottky barrier visualization utilizing computational modeling and ballistic electron emission microscopy. Journal of Applied Physics, 2018, 123, .	2.5	3
25	Mapping the Spin-Injection Probability on the Atomic Scale. Journal of Superconductivity and Novel Magnetism, 2002, 15, 37-42.	0.5	1
26	Magnetic and Structural Properties of Mn-implanted Si. Materials Research Society Symposia Proceedings, 2004, 853, 114.	0.1	1
27	Visualizing metal/HfO2/SiO2/Si(001) interface electrostatic barrier heights with ballistic hole emission microscopy. Journal of Applied Physics, 2019, 126, 195302.	2.5	1
28	Determination of the energetic resolution of Schottky barrier visualization via interface band structure and parallel momentum conservation. AIP Advances, 2021, 11, .	1.3	1
29	Simultaneous surface topography and spin-injection probability. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 67	1.6	Ο